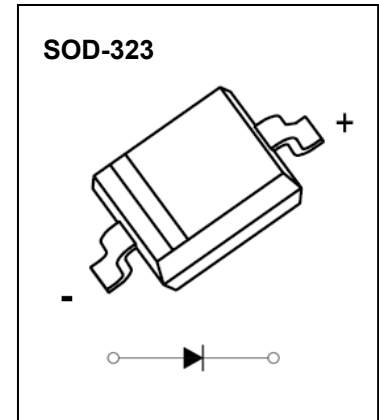


SOD-323 Plastic-Encapsulate Diodes

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING:SF



Maximum Ratings @Ta=25°C

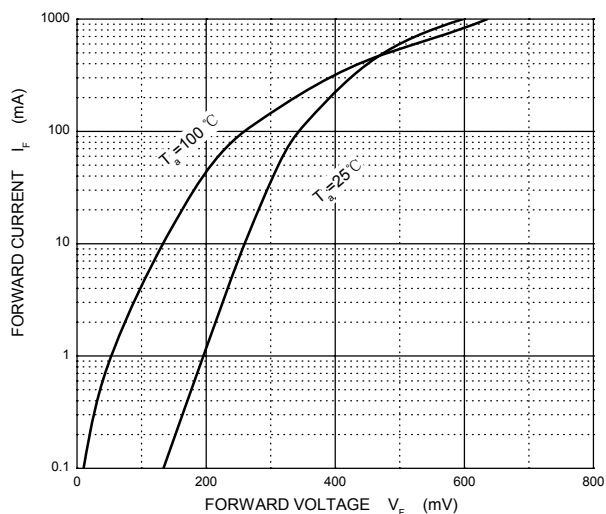
Parameter	Symbo	Value	Unit
Peak repetitive peak reverse voltage	V_{RRM}	40	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS reverse voltage reverse voltage (DC)	$V_{R(RMS)}$	28	V
Average rectified output current	I_o	0.5	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	5.5	A
Power dissipation	P_D	200	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	500	°C/W
Operating Junction Temperature Range	T_j	-40 ~ +125	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C
Voltage rate of change	dv/dt	1000	V/μs

Electrical Characteristics @Ta=25°C

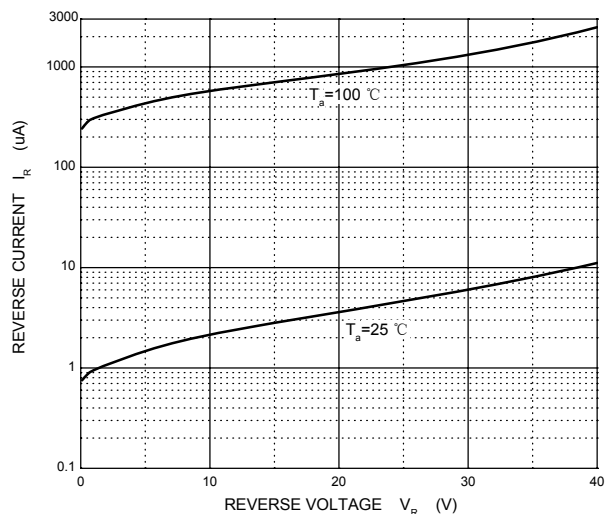
	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=20\mu A$	40		V
Reverse current	I_R	$V_R=20V$		10	uA
		$V_R=40V$		20	
Forward voltage	V_F	$I_F=0.5A$		0.51	V
		$I_F=1.0A$		0.62	
Capacitance between terminals	C_T	$V_R=0, f=1MHz$		170	pF

Typical Characteristics

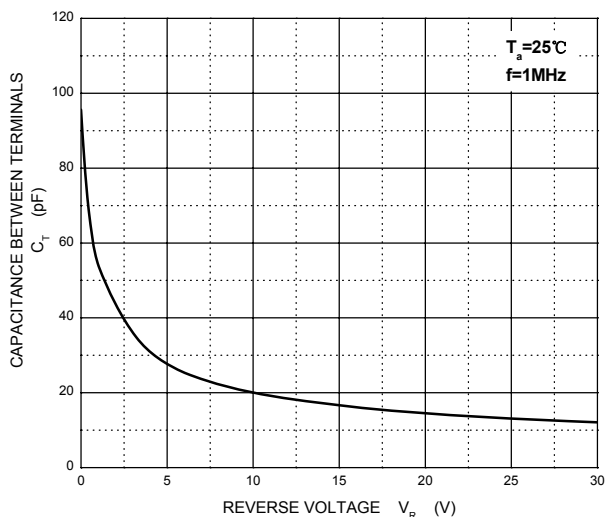
Forward Characteristics



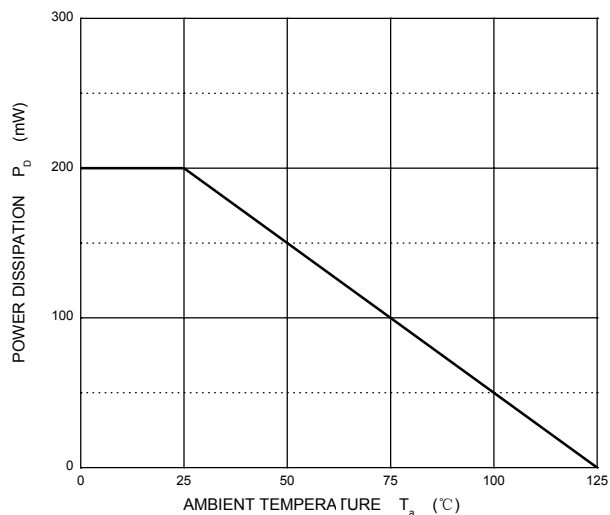
Reverse Characteristics

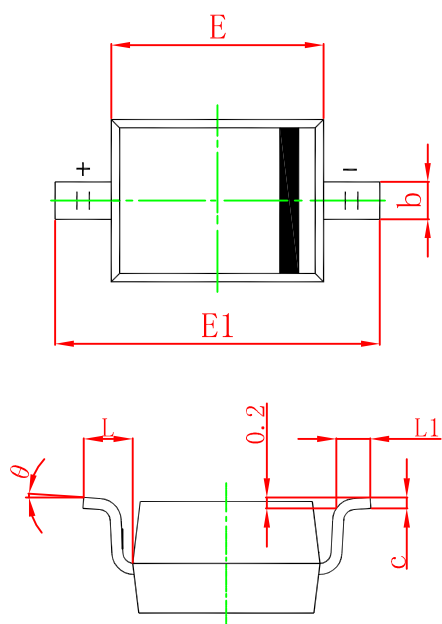


Capacitance Characteristics



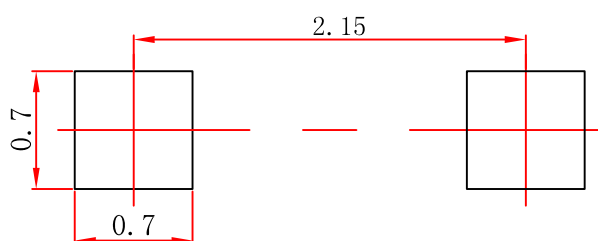
Power Derating Curve





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		1.100		0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.000	0.031	0.039
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.750	0.098	0.108
L	0.475 REF		0.019 REF	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.